

Silicon Phototransistors

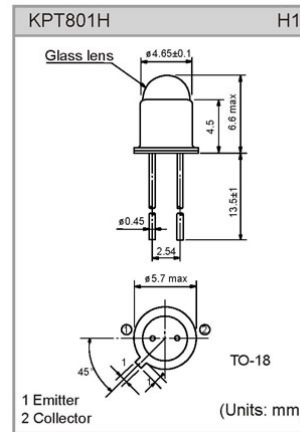
KPT801H

Features

- NPN phototransistor packaged in a 2 leads TO-18
- Glass lens
- Low leak current

Applications

- Optical switches
- Optical encoders
- Photo-isolator
- Camera stroboscopes
- Infrared sensors
- Automatic control apparatus



Specifications

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit	Conditions
Collector-emitter voltage	V_{CEO}	20	V	
Emitter-collector voltage	V_{ECO}	5	V	
Operating temperature	T_{opr}	-25 to +125		Avoid dew condensation
Storage temperature	T_{stg}	-55 to +150		Avoid dew condensation

Electrical and Optical characteristics

Parameter	Symbol	Value			Unit	Conditions
		Min.	Typ.	Max		
Sensitive size	S		0.64 x 0.64		mm	
Sensitive wavelength		700	800(p)	1000	V	p=Peak wavelength
Photocurrent	I_L		2		mA	$V_{CE}=5V, 100lx(@2856K)$
Dark current	I_D		100	200	nA	$V_{CE}=20V$
Current amplification factor	h_{FE}	600			-	$V_{CE}=5V, I_C=2mA$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.4	V	$I_C=0.1mA, 100lx(@2856K)$
Rise/Fall Time	tr,tf		5		μS	$V_{CE}=5V, I_C=2mA, R_L=100$
Half angle	2		17		deg	

